

1. General description

High voltage, high speed, planar passivated NPN power switching transistor with integrated anti-parallel E-C diode in a SOT428 (DPAK) surface mountable plastic package.

2. Features and benefits

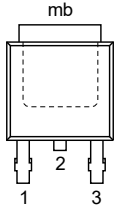
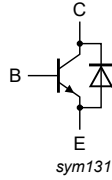
- Fast switching
- High voltage capability
- Integrated anti-parallel E-C diode
- Surface mountable package
- Very low switching and conduction losses

3. Applications

- DC-to-DC converters
- Electronic lighting ballasts
- Inverters
- Motor control systems

4. Pinning information

Table 1. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|---------------------------------------|---|---|
| 1 | B | base |  <p>DPAK (SOT428)</p> |  <p>sym131</p> |
| 2 | C | collector ^[1] | | |
| 3 | E | emitter | | |
| mb | C | mounting base; connected to collector | | |

[1] it is not possible to make a connection to pin 2 of the SOT428 (DPAK) package

5. Ordering information

Table 2. Ordering information

| Type number | Package | | |
|-------------|---------|---|---------|
| | Name | Description | Version |
| BUJD103AD | DPAK | plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped) | SOT428 |

6. Limiting values

Table 3. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|------------|--------------------------------|-------------------------------------|-----|-----|------|
| V_{CESM} | collector-emitter peak voltage | $V_{BE} = 0\text{ V}$ | - | 700 | V |
| V_{CBO} | collector-base voltage | $I_E = 0\text{ A}$ | - | 700 | V |
| V_{CEO} | collector-emitter voltage | $I_B = 0\text{ A}$ | - | 400 | V |
| I_C | collector current | DC; Fig. 1; Fig. 2; Fig. 3 | - | 4 | A |
| I_{CM} | peak collector current | Fig. 1; Fig. 2; Fig. 3 | - | 8 | A |
| I_B | base current | DC | - | 2 | A |
| I_{BM} | peak base current | | - | 4 | A |
| P_{tot} | total power dissipation | $T_{mb} \leq 25\text{ °C}$; Fig. 4 | - | 80 | W |
| T_{stg} | storage temperature | | -65 | 150 | °C |
| T_j | junction temperature | | - | 150 | °C |

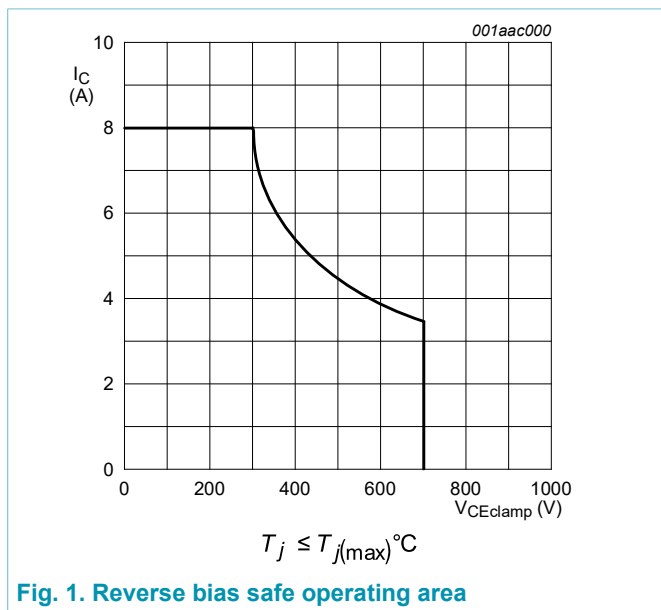


Fig. 1. Reverse bias safe operating area

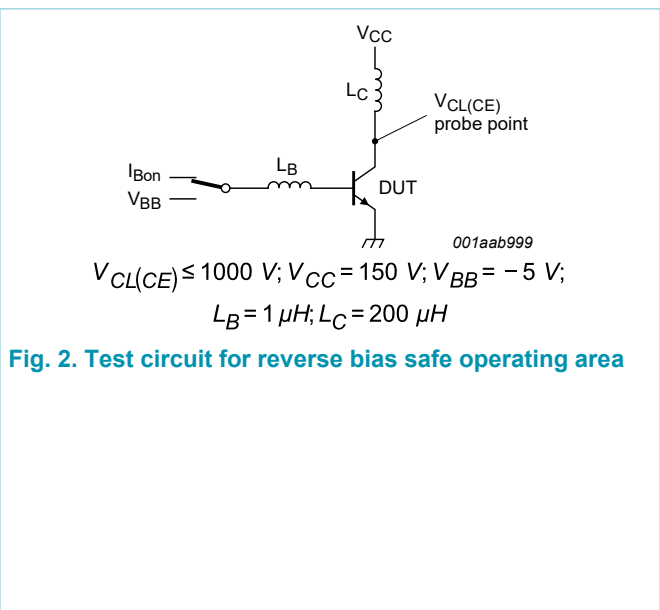
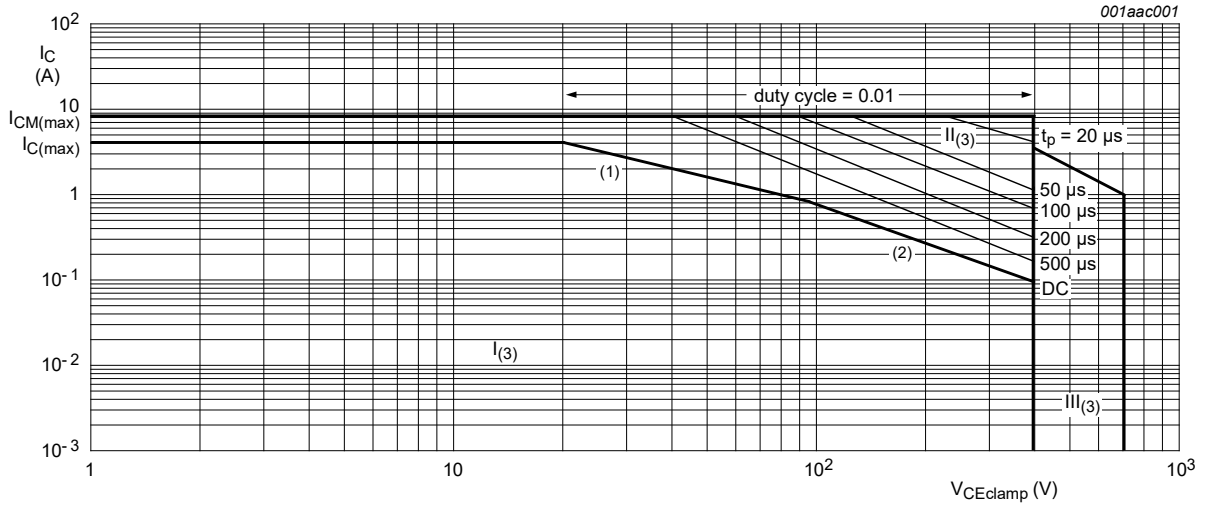
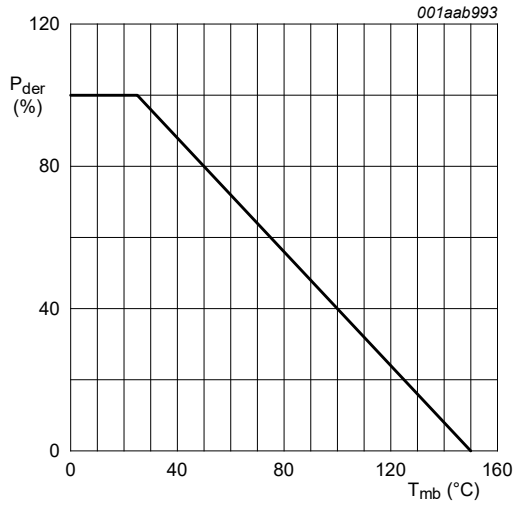


Fig. 2. Test circuit for reverse bias safe operating area



- 1) P_{tot} maximum and P_{tot} peak maximum lines
- 2) Second breakdown limits
- 3) I = Region of permissible DC operation
- II = Extension for repetitive pulse operation
- III = Extension during turn-on in single transistor converters provided that $R_{BE} \leq 100 \Omega$ and $t_p \leq 0.6 \mu s$

Fig. 3. Forward bias safe operating area for $T_{mb} \leq 25 \text{ }^\circ\text{C}$



$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ\text{C})}} \times 100 \%$$

Fig. 4. Normalized total power dissipation as a function of mounting base temperature

7. Thermal characteristics

Table 4. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|----------------|--|--|-----|-----|------|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | Fig. 5 | - | - | 1.56 | K/W |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient free air | printed circuit board (FR4) mounted; minimum footprint; Fig. 6 | - | 75 | - | K/W |

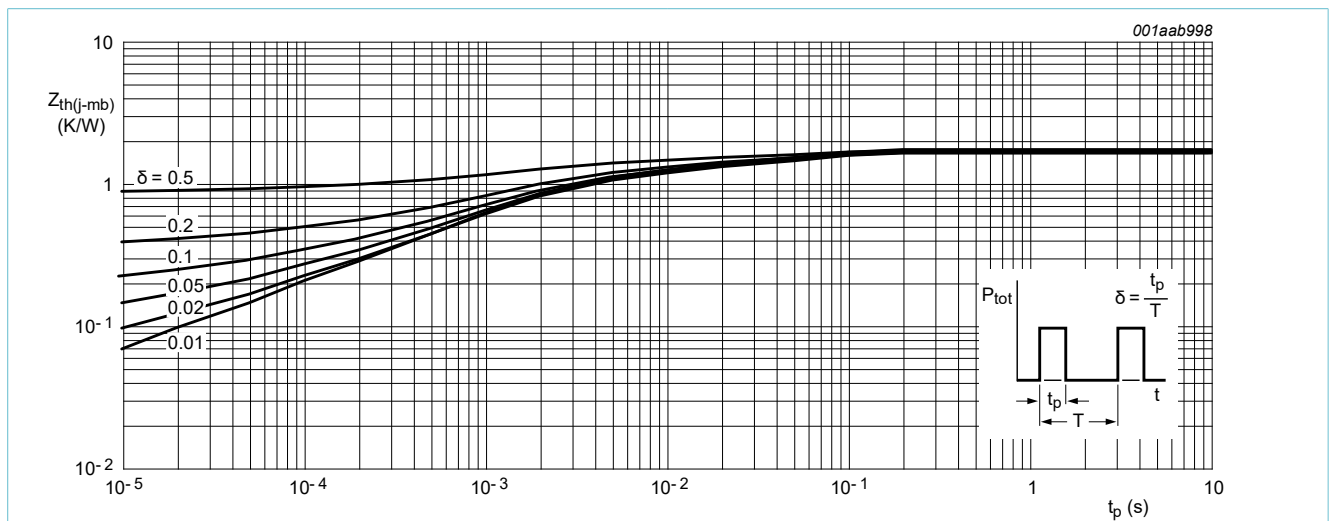


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse width

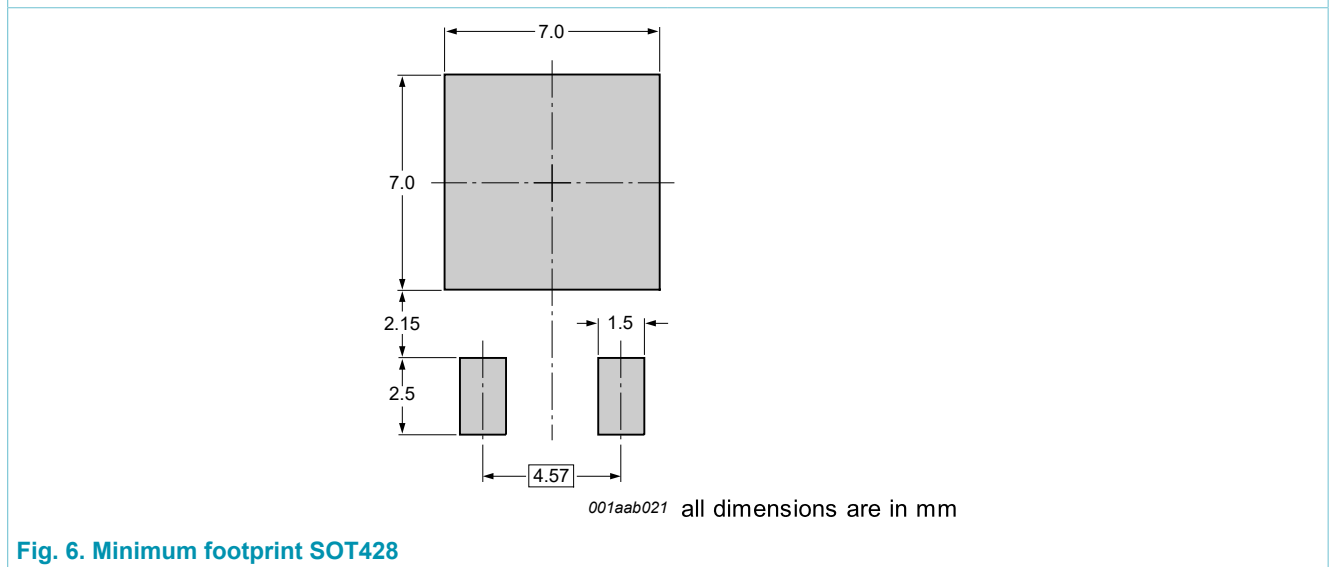


Fig. 6. Minimum footprint SOT428

8. Characteristics

Table 5. Characteristics

| Symbol | Parameter | Conditions | | Min | Typ | Max | Unit | |
|--------------------------------|--|---|--|-----|------|------|---------------|---------------|
| Static characteristics | | | | | | | | |
| I_{CES} | collector-emitter cut-off current (base shorted) | $V_{BE} = 0\text{ V}; V_{CE} = 700\text{ V}; T_j = 125\text{ }^\circ\text{C}$ | [1] | - | - | 2 | mA | |
| | | $V_{BE} = 0\text{ V}; V_{CE} = 700\text{ V}; T_j = 25\text{ }^\circ\text{C}$ | [1] | - | - | 1 | mA | |
| I_{CBO} | collector-base cut-off current (emitter open) | $V_{CB} = 700\text{ V}; I_E = 0\text{ A}$ | [1] | - | - | 1 | mA | |
| I_{CEO} | collector-emitter cut-off current (base open) | $V_{CE} = 400\text{ V}; I_B = 0\text{ A}$ | [1] | - | - | 0.1 | mA | |
| I_{EBO} | emitter-base cut-off current (collector open) | $V_{EB} = 7\text{ V}; I_C = 0\text{ A}$ | | - | - | 10 | mA | |
| V_{CEsat} | collector-emitter saturation voltage | $I_C = 3\text{ A}; I_B = 0.6\text{ A};$ Fig. 7 ; Fig. 8 | | - | 0.29 | 1 | V | |
| V_{BEsat} | base-emitter saturation voltage | $I_C = 3\text{ A}; I_B = 0.6\text{ A};$ Fig. 9 | | - | 0.99 | 1.5 | V | |
| V_F | forward voltage | $I_F = 2\text{ A}; T_j = 25\text{ }^\circ\text{C}$ | | - | 1.04 | 1.5 | V | |
| h_{FE} | DC current gain | $I_C = 1\text{ mA}; V_{CE} = 5\text{ V}; T_{mb} = 25\text{ }^\circ\text{C};$ Fig. 10 | | 10 | 15 | 32 | | |
| | | $I_C = 500\text{ mA}; V_{CE} = 5\text{ V}; T_{mb} = 25\text{ }^\circ\text{C};$ Fig. 10 | | 13 | 21 | 32 | | |
| | | $I_C = 2\text{ A}; V_{CE} = 5\text{ V}; T_{mb} = 25\text{ }^\circ\text{C};$ Fig. 10 | | 11 | 16 | 22 | | |
| | | $I_C = 3\text{ A}; V_{CE} = 5\text{ V}; T_{mb} = 25\text{ }^\circ\text{C};$ Fig. 10 | | - | 12.5 | - | | |
| Dynamic characteristics | | | | | | | | |
| t_{on} | turn-on time | $I_C = 2.5\text{ A}; I_{Bon} = 0.5\text{ A}; I_{Boff} = -0.5\text{ A};$ $R_L = 75\text{ }\Omega; T_j = 25\text{ }^\circ\text{C};$ resistive load; Fig. 11 ; Fig. 12 | | - | 0.52 | 0.6 | μs | |
| t_s | storage time | | $I_C = 2\text{ A}; I_{Bon} = 0.4\text{ A}; V_{BB} = -5\text{ V};$ $L_B = 1\text{ }\mu\text{H}; T_j = 25\text{ }^\circ\text{C};$ inductive load; Fig. 13 ; Fig. 14 | | - | 1.2 | 1.4 | μs |
| | | | $I_C = 2\text{ A}; I_{Bon} = 0.4\text{ A}; V_{BB} = -5\text{ V};$ $L_B = 1\text{ }\mu\text{H}; T_j = 100\text{ }^\circ\text{C};$ inductive load; Fig. 13 ; Fig. 14 | | - | - | 1.8 | μs |
| t_f | fall time | $I_C = 2.5\text{ A}; I_{Bon} = 0.5\text{ A}; I_{Boff} = -0.5\text{ A};$ $R_L = 75\text{ }\Omega;$ resistive load; Fig. 11 ; Fig. 12 | | - | 0.3 | 0.35 | μs | |
| | | $I_C = 2\text{ A}; I_{Bon} = 0.4\text{ A}; V_{BB} = -5\text{ V};$ $L_B = 1\text{ }\mu\text{H};$ inductive load; Fig. 13 ; Fig. 14 | | - | - | 0.12 | μs | |
| | | | | - | 0.03 | 0.06 | μs | |

[1] Measured with half-sine wave voltage (curve tracer)

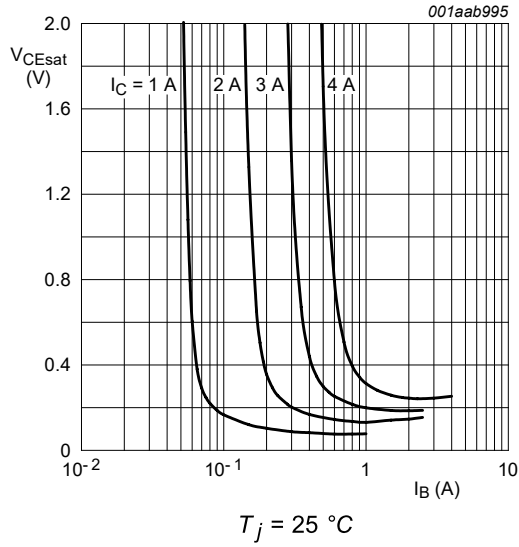


Fig. 7. Collector-emitter saturation voltage as a function of base current; typical values

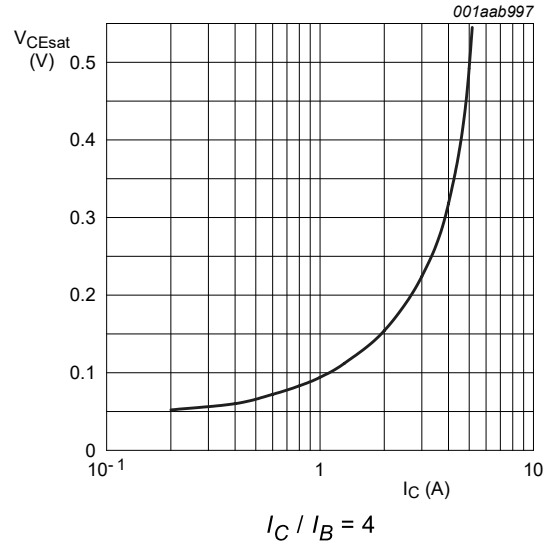


Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

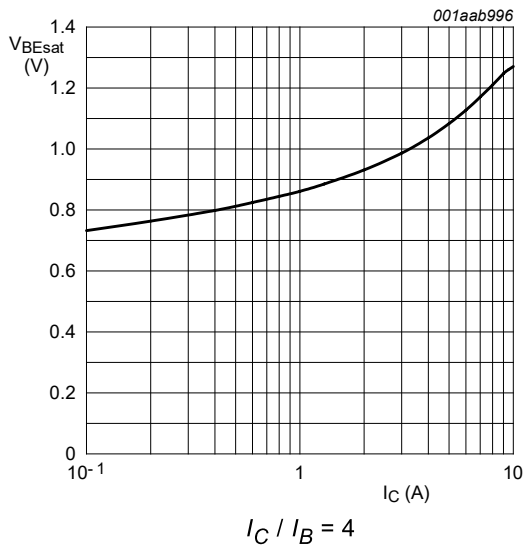


Fig. 9. Base-emitter saturation voltage as a function of collector current; typical values

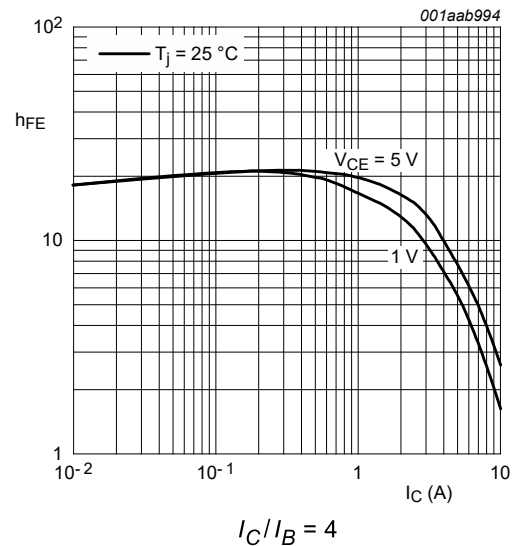
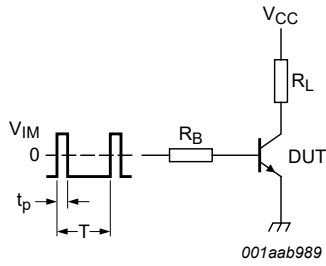


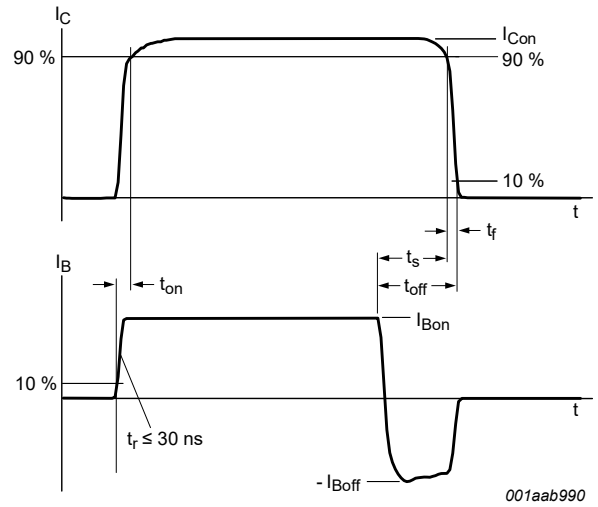
Fig. 10. DC current gain as a function of collector current; typical values



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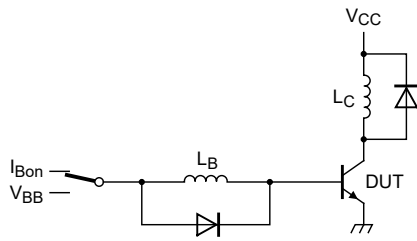
$V_{IM} = -6 \text{ to } +8 \text{ V}; V_{CC} = 250 \text{ V}; t_p = 20 \mu\text{s}; \delta = \frac{t_p}{T} = 0.01$
 R_B and R_L calculated from I_{Con} and I_{Bon} requirements.

Fig. 11. Test circuit for resistive load switching



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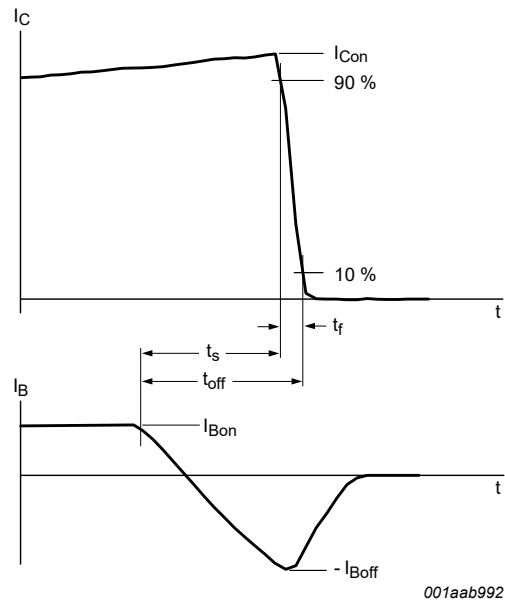
Fig. 12. Switching times waveforms for resistive load



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$V_{CC} = 300 \text{ V}; V_{BB} = -5 \text{ V}; L_C = 200 \mu\text{H}; L_B = 1 \mu\text{H}$

Fig. 13. Test circuit for inductive load switching



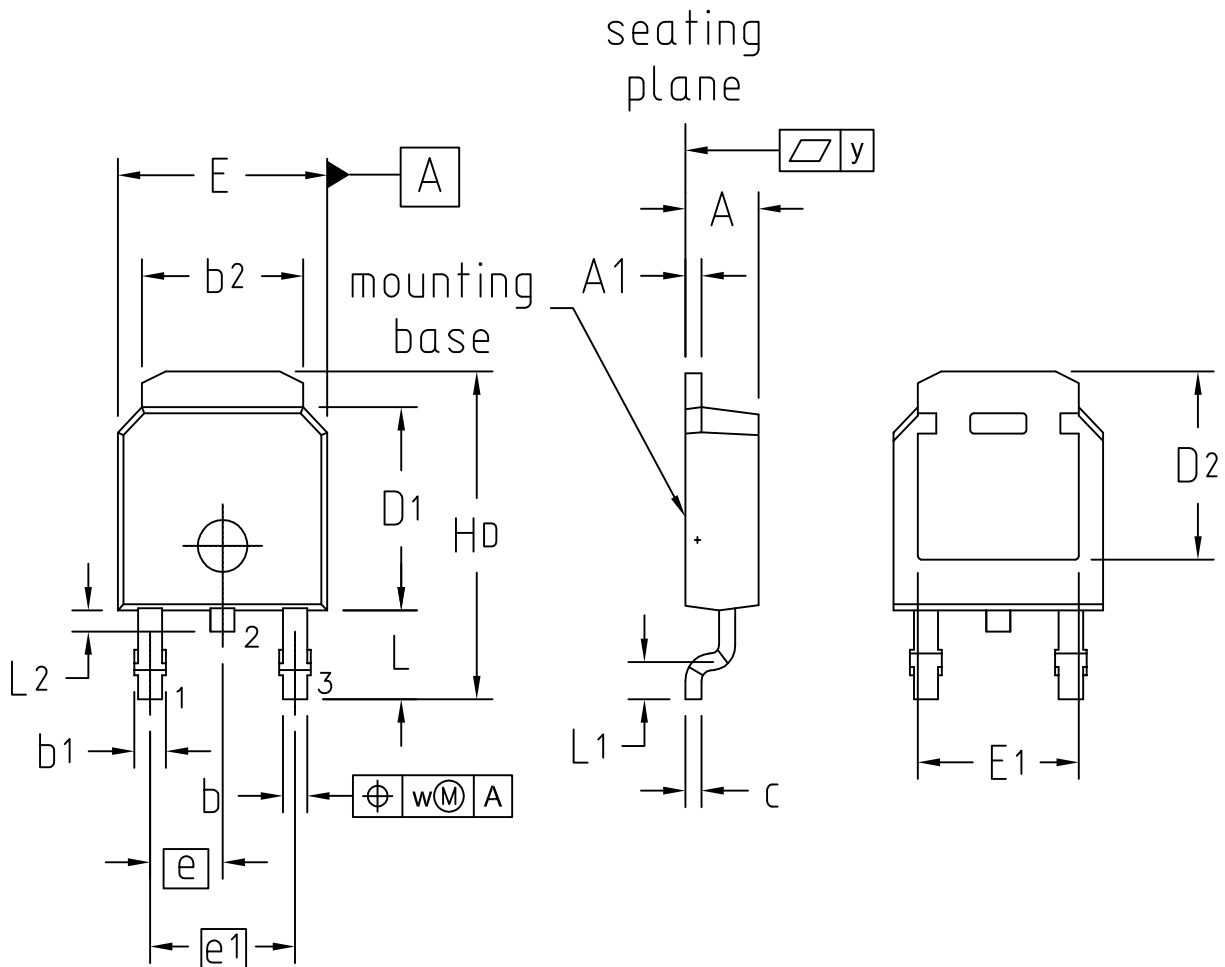
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Fig. 14. Switching times waveforms for inductive load

9. Package outline

Plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)

SOT428



| UNIT | A | A ₁ | b | b ₁ | b ₂ | c | D ₁ | D ₂ | E | E ₁ | e | e ₁ | H _d | L | L ₁ | L ₂ | w | y |
|------|------|----------------|------|----------------|----------------|------|----------------|----------------|------|----------------|-------|----------------|----------------|------|----------------|----------------|-----|------|
| mm | 2.38 | 0.93 | 0.89 | 1.1 | 5.46 | 0.56 | 6.22 | 4.00 | 6.73 | 4.45 | 2.285 | 4.57 | 10.40 | 2.95 | 0.5 | 0.90 | 0.2 | 0.20 |
| | 2.22 | 0.46 | 0.71 | 0.9 | 5.00 | 0.20 | 5.98 | min. | 6.47 | min. | | | 9.60 | 2.55 | min. | 0.50 | 0.2 | max. |

| OUTLINE VERSION | REFERENCES | | | | EUROPEAN PROJECTION | ISSUE DATE |
|-----------------|------------|--------|------|--|---------------------|------------|
| | IEC | JEDEC | EIAJ | | | |
| SOT428 | | TO-252 | | | | |

Fig. 15. Package outline DPAK (SOT428)

10. Legal information

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|--------------------------------|--------------------|---|
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Date of release: 11 October 2016



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